

Silicon PNP Power Transistors

2SA1667 2SA1668

DESCRIPTION

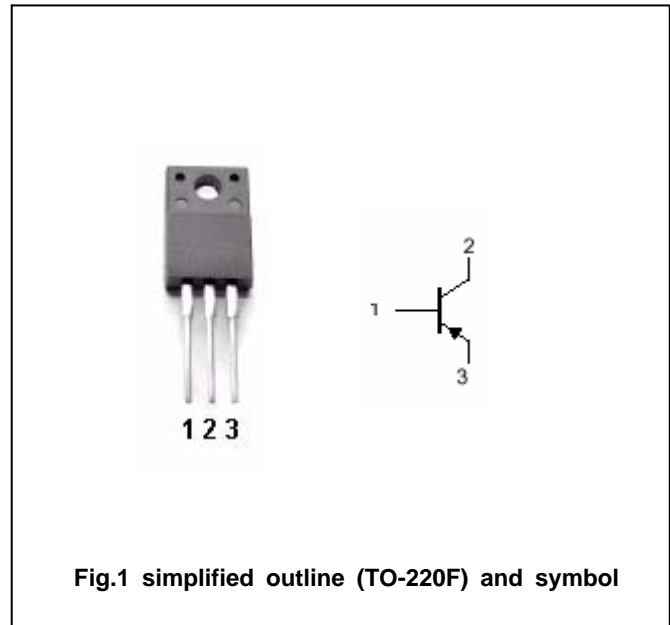
- With TO-220F package
- Complement to type 2SC4381/4382

APPLICATIONS

- For TV vertical output ,audio output driver and general purpose applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings (Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	2SA1667	-150	V
		2SA1668	-200	
V _{CEO}	Collector-emitter voltage	2SA1667	-150	V
		2SA1668	-200	
V _{EBO}	Emitter-base voltage	Open collector	-6	V
I _C	Collector current		-2	A
I _B	Base current		-1	A
P _C	Collector dissipation	T _C =25	25	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT	
V _{(BR)CEO}	Collector-emitter breakdown voltage	2SA1667	I _C =-25mA ; I _B =0	-150			V
		2SA1668		-200			
V _{CEsat}	Collector-emitter saturation voltage	I _C =-0.7A; I _B =-70mA			-1.0	V	
I _{CBO}	Collector cut-off current	2SA1667	V _{CB} =-150V; I _E =0			-10	μA
		2SA1668	V _{CB} =-200V; I _E =0			-10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-6V; I _C =0			-10	μA	
h _{FE}	DC current gain	I _C =-0.7A ; V _{CE} =-10V	60				
f _T	Transition frequency	I _C =-0.2A ; V _{CE} =-12V		20		MHz	
C _{OB}	Output capacitance	I _E =0 ; V _{CB} =10V; f=1MHz		60		pF	

Switching time

t _{on}	Turn-on time	I _C =-1A ; I _{B1} =-I _{B2} =-0.1A V _{CC} =-20V , R _L =20		0.40		μs
t _s	Storage time			1.50		μs
t _f	Fall time			0.50		μs

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PACKAGE OUTLINE

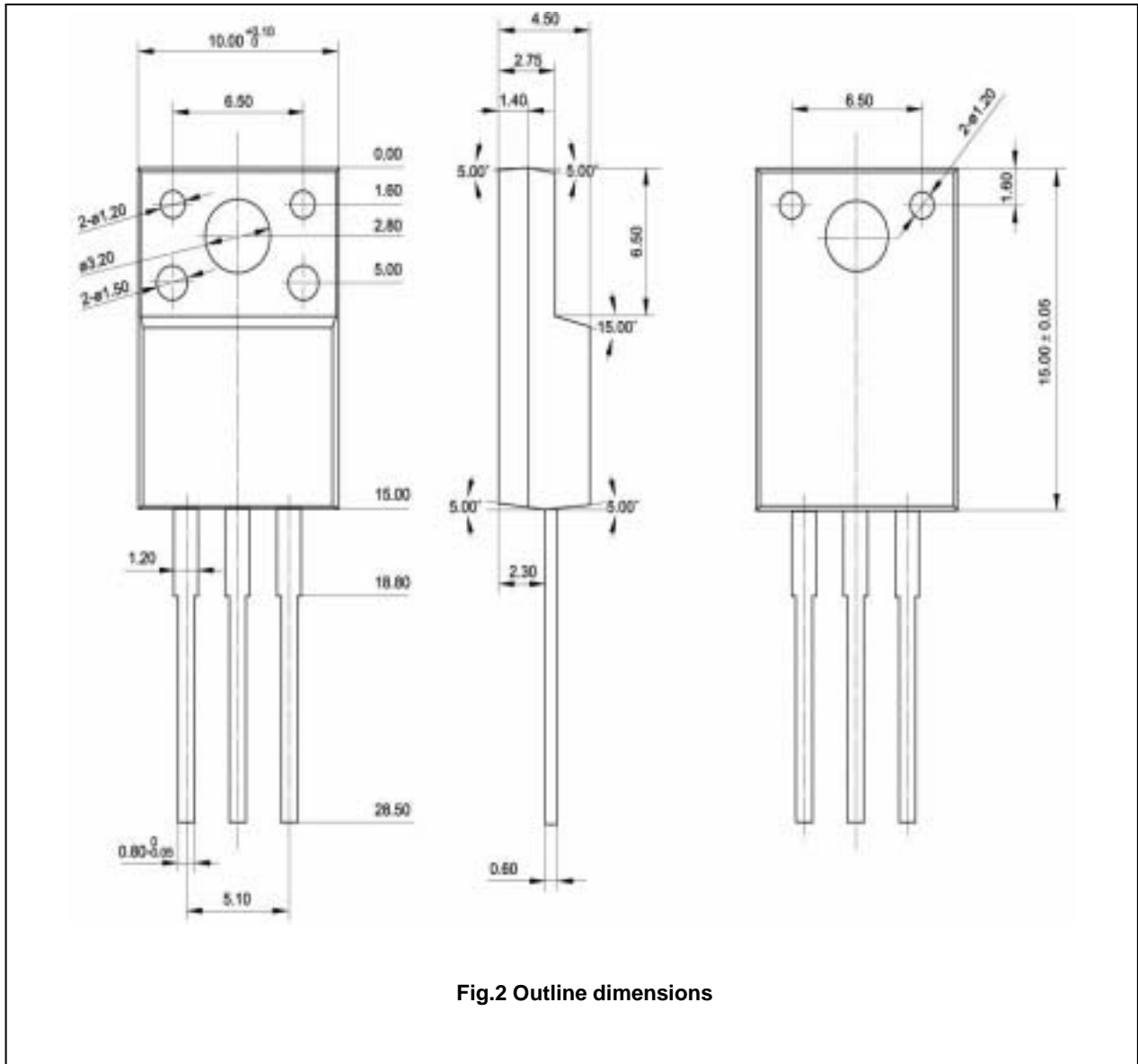


Fig.2 Outline dimensions

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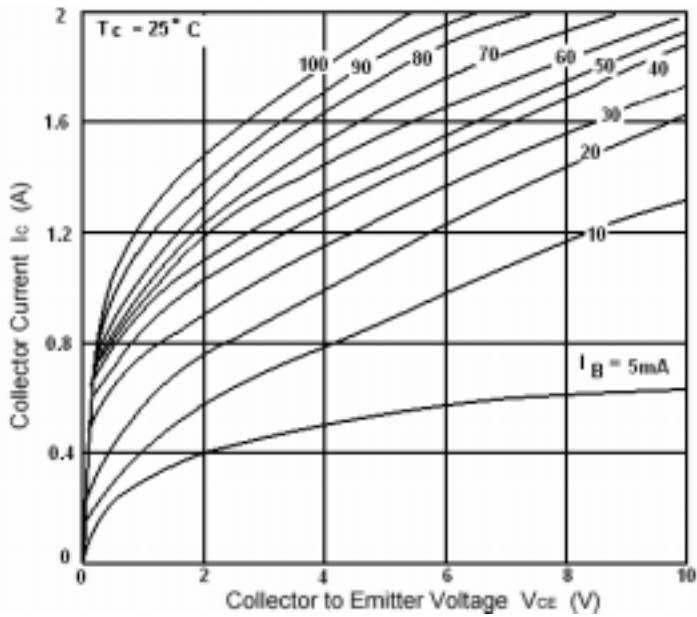


Fig.3 Static Characteristic

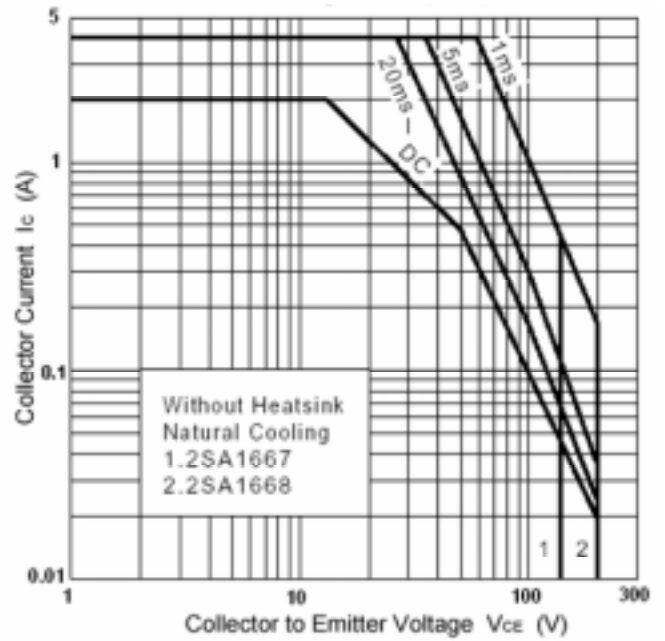


Fig.4 Safe Operating Area

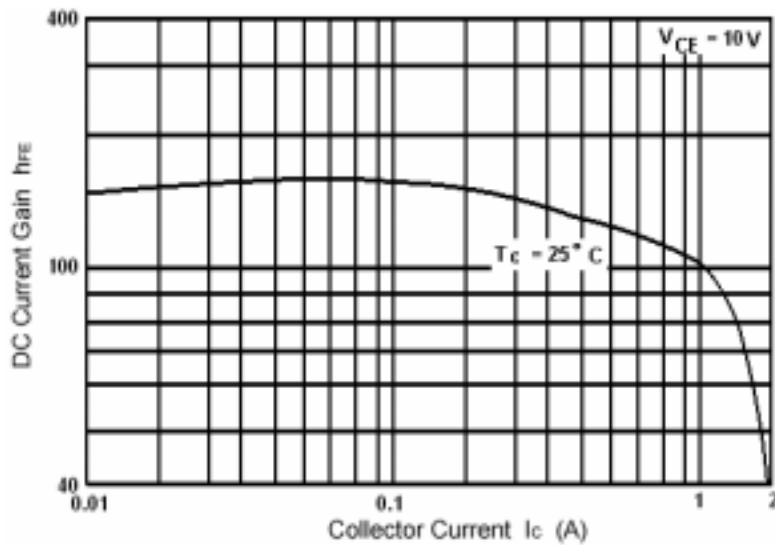


Fig.5 DC current Gain